

General Description

The WST3417 is the highest performance trench P-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The WST3417 meet the RoHS and Green Product requirement, with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

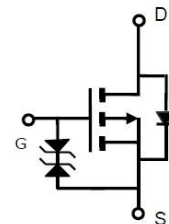
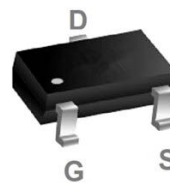
Product Summary

BVDSS	RDSON	ID
-20V	47mΩ	-4.6A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- ESD:3KV

SOT-23N Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-4.6	A
$I_D@T_C=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-3.0	A
I_{DM}	Pulsed Drain Current ²	-17	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1.0	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	110	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	70	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.016	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-3A	---	47	55	mΩ
		V _{GS} =-2.5V, I _D =-2A	---	55	70	
		V _{GS} =-1.8V, I _D =-1A	---	68	85	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.3	-0.75	-1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	3.97	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±8V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	---	14	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-3A	---	6.2	9	nC
Q _{gs}	Gate-Source Charge		---	2.2	2.5	
Q _{gd}	Gate-Drain Charge		---	1.8	2.6	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-10V, V _{GS} =-4.5V, R _G =3.3Ω, I _D =-3A	---	2.7	5.5	ns
T _r	Rise Time		---	8.4	15	
T _{d(off)}	Turn-Off Delay Time		---	38	78	
T _f	Fall Time		---	6	12	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	575	810	pF
C _{oss}	Output Capacitance		---	98	135	
C _{rss}	Reverse Transfer Capacitance		---	75	110	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-1	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	-17	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1	V
t _{rr}	Reverse Recovery Time	I _F =-3A, dI/dt=100A/μs, T _J =25°C	---	28	---	nS
Q _{rr}	Reverse Recovery Charge		---	25	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

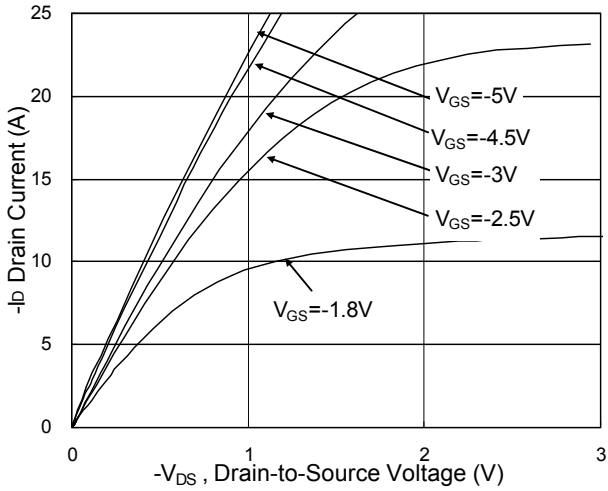


Fig.1 Typical Output Characteristics

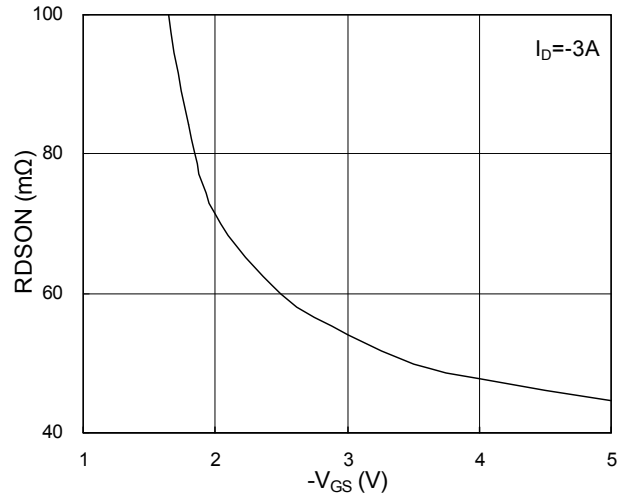


Fig.2 On-Resistance vs. G-S Voltage

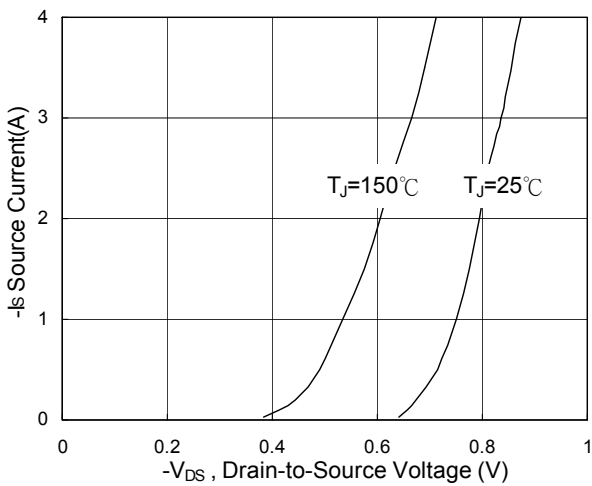


Fig.3 Forward Characteristics of Reverse

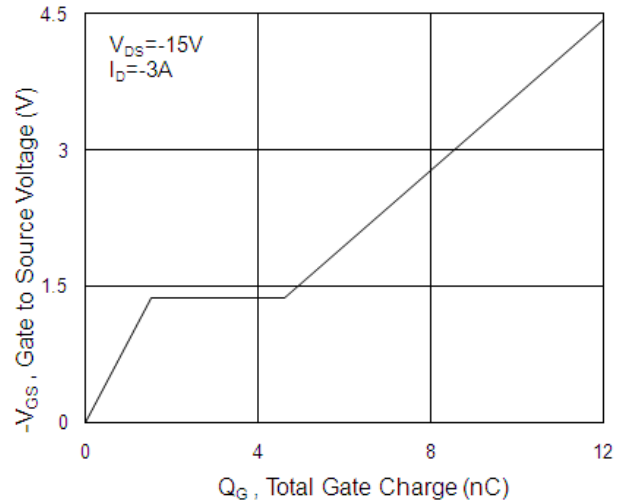


Fig.4 Gate-Charge Characteristics

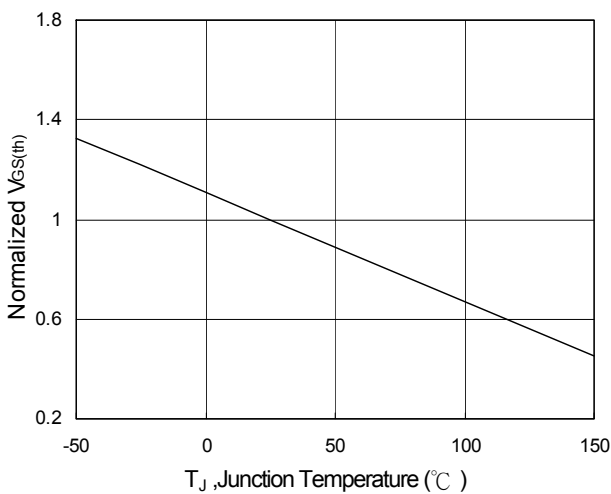


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

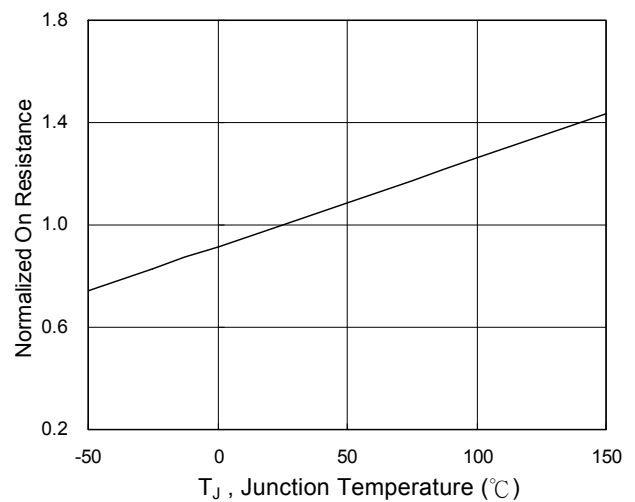


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

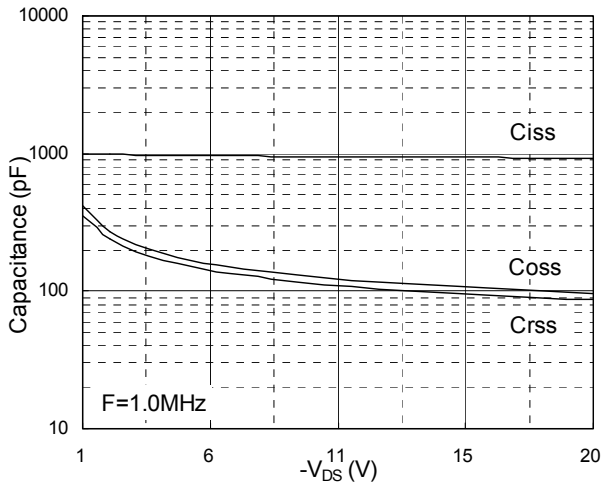


Fig.7 Capacitance

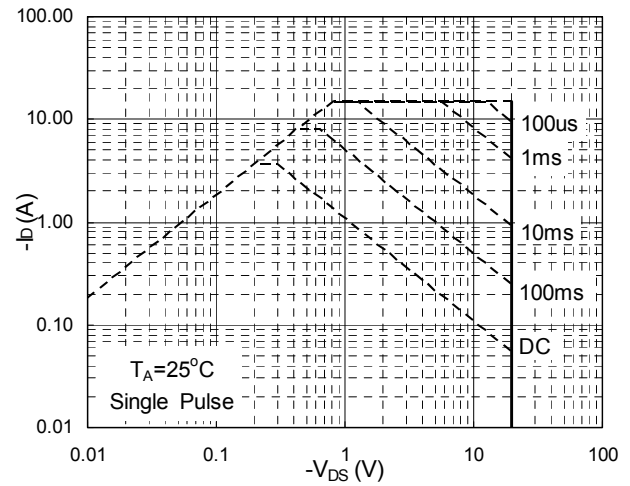


Fig.8 Safe Operating Area

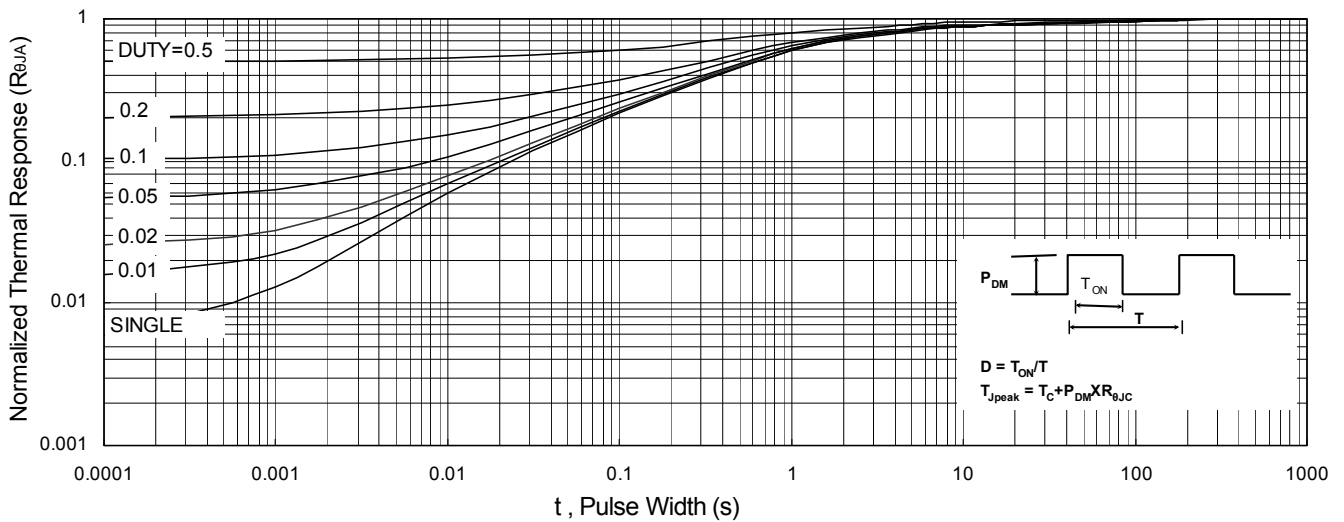


Fig.9 Normalized Maximum Transient Thermal Impedance

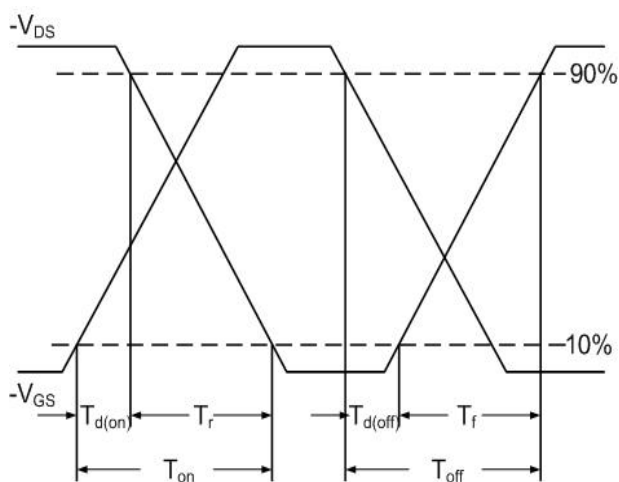


Fig.10 Switching Time Waveform

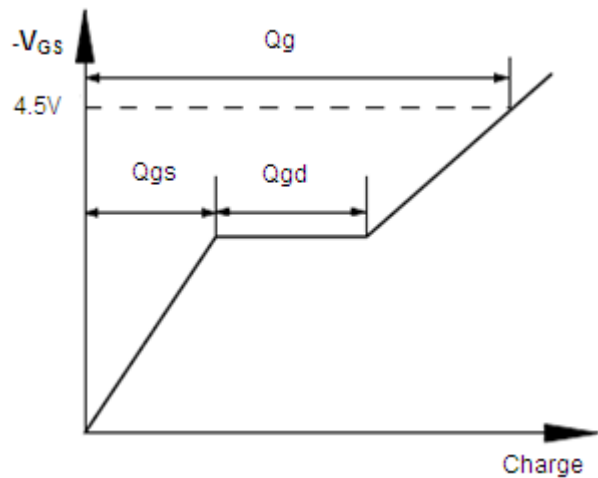


Fig.11 Gate Charge Waveform